

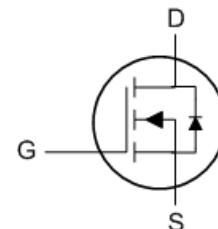
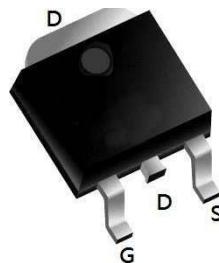
- ★ Super Low Gate Charge
- ★ 100% EAS Guaranteed
- ★ Green Device Available
- ★ Excellent CdV/dt effect decline
- ★ Advanced high cell density Trench technology

Product Summary

BVDSS	RDS(on)	ID
60V	6mΩ	80A

Description

The XR6080 is the high performance complementary N-ch MOSFETs with high cell density, which provide excellent RDS(on) and gate charge for most of the synchronous buck converter applications. The XR6080 meet the RoHS and Green Product requirement 100% EAS guaranteed with full function reliability approved.

TO252-3L Pin Configuration**Absolute Maximum Ratings** ($T_c=25^\circ\text{C}$ unless otherwise specified)

Symbol	Parameter		Max.	Units
V_{DSS}	Drain-Source Voltage		60	V
V_{GSS}	Gate-Source Voltage		± 25	V
I_D	Continuous Drain Current	$T_c = 25^\circ\text{C}$	80	A
		$T_c = 100^\circ\text{C}$	52	A
I_{DM}	Pulsed Drain Current ^{note1}		320	A
EAS	Single Pulsed Avalanche Energy ^{note2}		169	mJ
P_D	Power Dissipation	$T_c = 25^\circ\text{C}$	108	W
R_{eJC}	Thermal Resistance, Junction to Case		1.4	$^\circ\text{C}/\text{W}$
T_J, T_{STG}	Operating and Storage Temperature Range		-55 to +175	°C

Electrical Characteristics ($T_J=25^\circ\text{C}$ unless otherwise specified)

Symbol	Parameter	Test Condition	Min.	Typ.	Max.	Units
Off Characteristic						
$V_{(\text{BR})\text{DSS}}$	Drain-Source Breakdown Voltage	$V_{GS}=0\text{V}$, $I_D=250\mu\text{A}$	60	-	-	V
I_{DSS}	Zero Gate Voltage Drain Current	$V_{DS}=60\text{V}$, $V_{GS}=0\text{V}$,	-	-	1.0	μA
I_{GSS}	Gate to Body Leakage Current	$V_{DS}=0\text{V}$, $V_{GS}=\pm 20\text{V}$	-	-	± 100	nA
On Characteristics						
$V_{GS(\text{th})}$	Gate Threshold Voltage	$V_{DS}=V_{GS}$, $I_D=250\mu\text{A}$	2	3	4	V
$R_{DS(\text{on})}$	Static Drain-Source on-Resistance note3	$V_{GS}=10\text{V}$, $I_D=30\text{A}$	-	5.3	7	$\text{m}\Omega$
Dynamic Characteristics						
C_{iss}	Input Capacitance	$V_{DS}=30\text{V}$, $V_{GS}=0\text{V}$, $f=1.0\text{MHz}$	-	4136	-	pF
C_{oss}	Output Capacitance		-	286	-	pF
C_{rss}	Reverse Transfer Capacitance		-	257	-	pF
Q_g	Total Gate Charge	$V_{DS}=30\text{V}$, $I_D=30\text{A}$, $V_{GS}=10\text{V}$	-	90	-	nC
Q_{gs}	Gate-Source Charge		-	9	-	nC
Q_{gd}	Gate-Drain("Miller") Charge		-	18	-	nC
Switching Characteristics						
$t_{d(on)}$	Turn-on Delay Time	$V_{DS}=30\text{V}$, $I_D=30\text{A}$, $R_G=1.8\Omega$, $V_{GS}=10\text{V}$	-	9	-	ns
t_r	Turn-on Rise Time		-	7	-	ns
$t_{d(off)}$	Turn-off Delay Time		-	40	-	ns
t_f	Turn-off Fall Time		-	15	-	ns
Drain-Source Diode Characteristics and Maximum Ratings						
I_S	Maximum Continuous Drain to Source Diode Forward Current	-	-	80	-	A
I_{SM}	Maximum Pulsed Drain to Source Diode Forward Current	-	-	320	-	A
V_{SD}	Drain to Source Diode Forward Voltage	$V_{GS}=0\text{V}$, $I_S=30\text{A}$	-	-	1.2	V
trr	Body Diode Reverse Recovery Time	$I_F=30\text{A}$, $dI/dt=100\text{A}/\mu\text{s}$	-	33	-	ns
Qrr	Body Diode Reverse Recovery Charge		-	46	-	nC

Notes:1. Repetitive Rating: Pulse Width Limited by Maximum Junction Temperature

2. EAS condition : $T_J=25^\circ\text{C}$, $V_{DD}=30\text{V}$, $V_G=10\text{V}$, $L=0.5\text{mH}$, $R_g=25\Omega$, $I_{AS}=26\text{A}$ 3. Pulse Test: Pulse Width $\leq 300\mu\text{s}$, Duty Cycle $\leq 0.5\%$

Typical Performance Characteristics

Figure 1: Output Characteristics

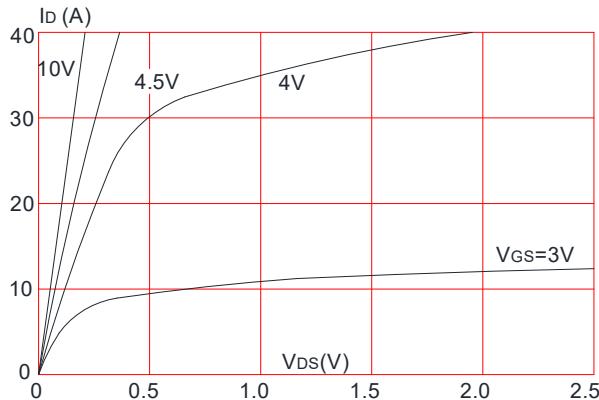


Figure 3: On-resistance vs. Drain Current

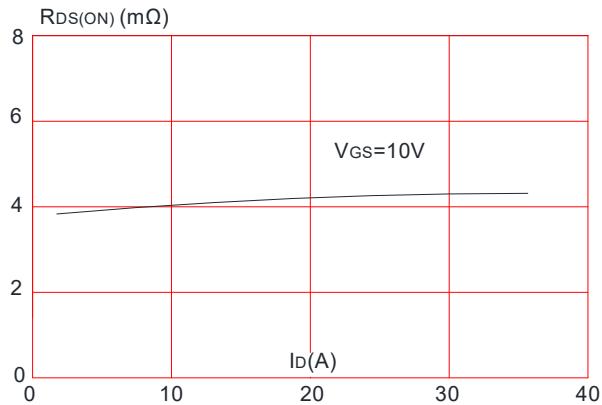


Figure 5: Gate Charge Characteristics

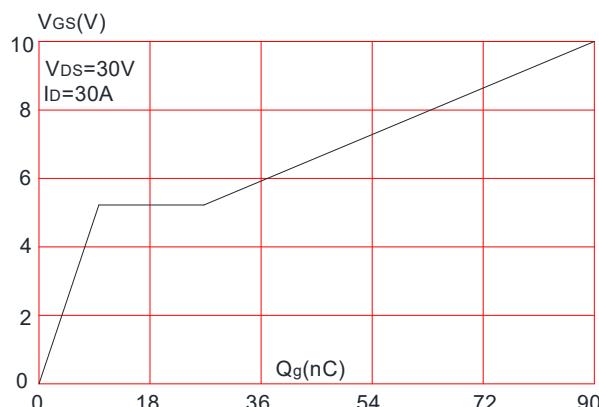


Figure 2: Typical Transfer Characteristics

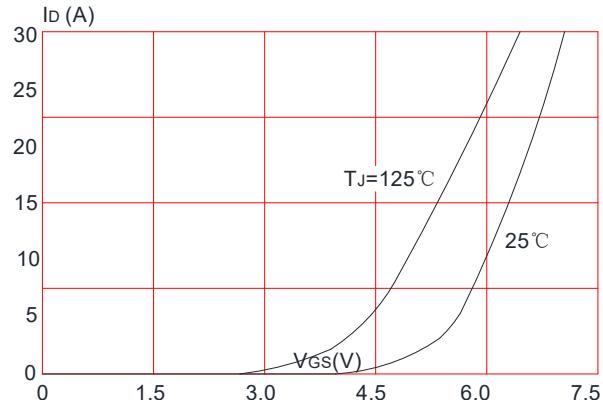


Figure 4: Body Diode Characteristics

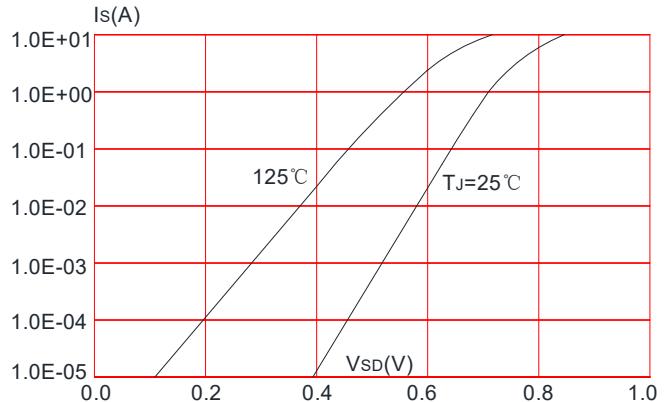
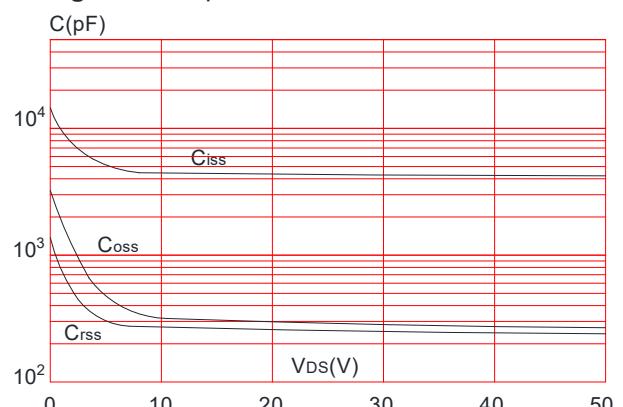
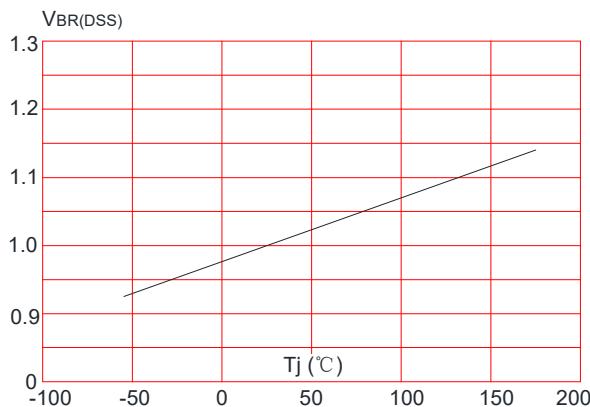
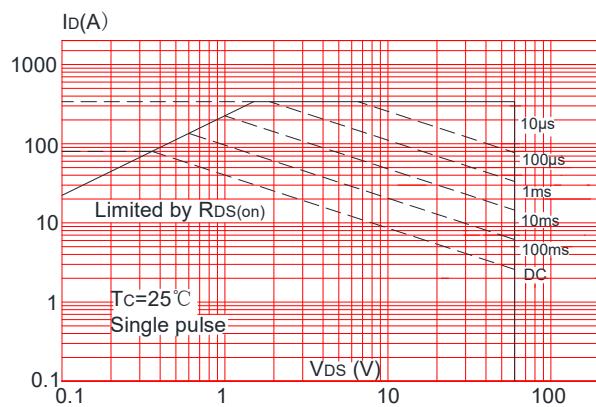
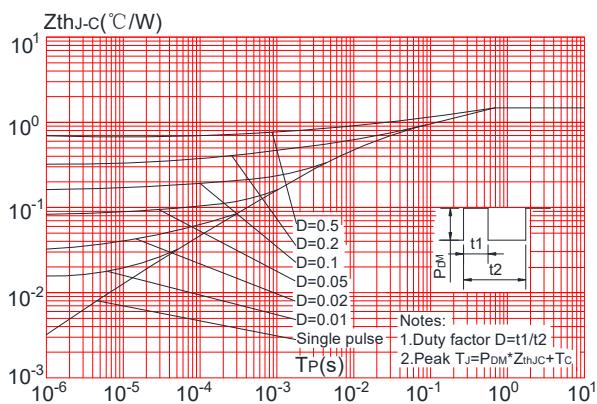
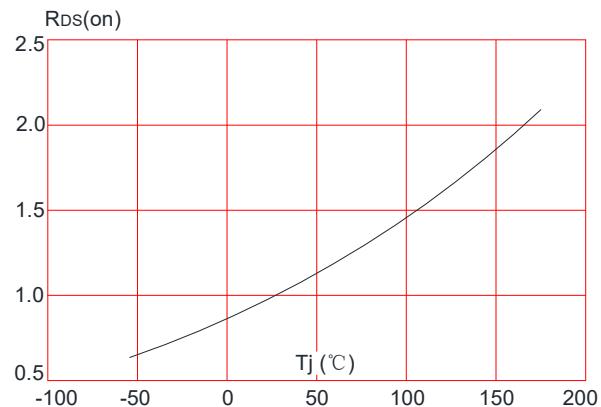
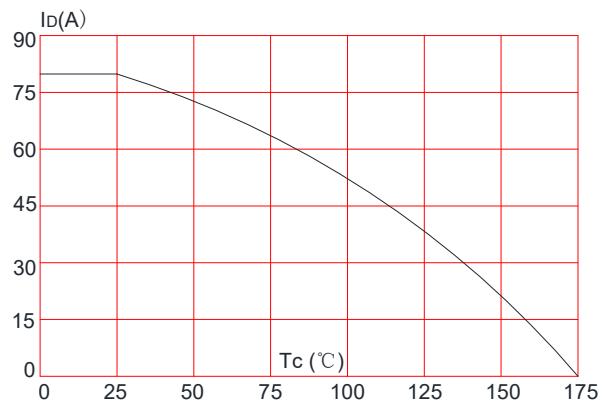


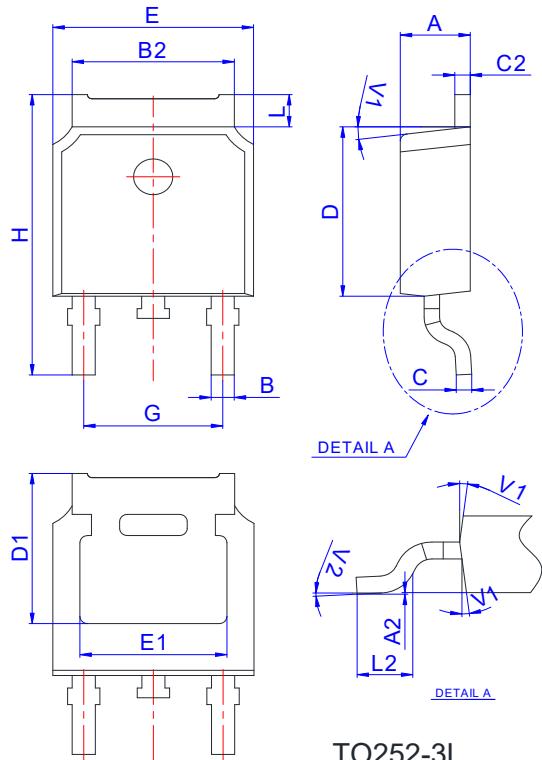
Figure 6: Capacitance Characteristics



N-Ch 60V Fast Switching MOSFETs

Figure 7: Normalized Breakdown Voltage vs. Junction Temperature**Figure 9:** Maximum Safe Operating Area**Figure 11:** Maximum Effective Transient Thermal Impedance, Junction-to-Case**Figure 8:** Normalized on Resistance vs. Junction Temperature**Figure 10:** Maximum Continuous Drain Current vs. Case Temperature

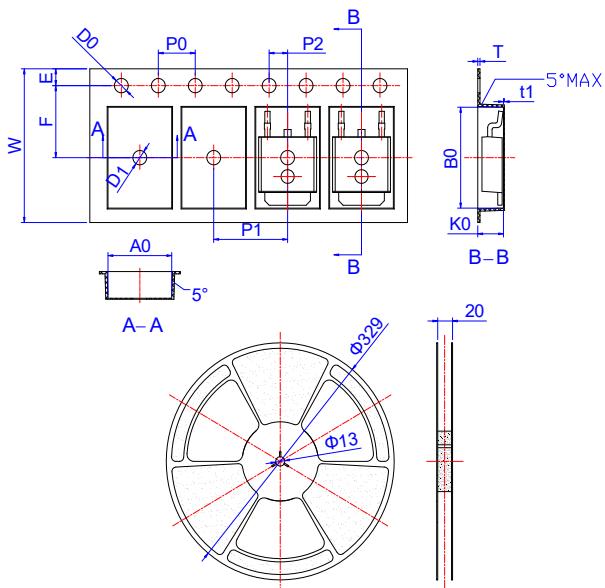
Package Mechanical Data-TO252-3L



TO252-3L

Ref.	Dimensions					
	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A	2.10		2.50	0.083		0.098
A2	0		0.10	0		0.004
B	0.66		0.86	0.026		0.034
B2	5.18		5.48	0.202		0.216
C	0.40		0.60	0.016		0.024
C2	0.44		0.58	0.017		0.023
D	5.90		6.30	0.232		0.248
D1	5.30REF			0.209REF		
E	6.40		6.80	0.252		0.268
E1	4.63			0.182		
G	4.47		4.67	0.176		0.184
H	9.50		10.70	0.374		0.421
L	1.09		1.21	0.043		0.048
L2	1.35		1.65	0.053		0.065
V1		7°			7°	
V2	0°		6°	0°		6°

Reel Specification-TO252-3L



Ref.	Dimensions					
	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
W	15.90	16.00	16.10	0.626	0.630	0.634
E	1.65	1.75	1.85	0.065	0.069	0.073
F	7.40	7.50	7.60	0.291	0.295	0.299
D0	1.40	1.50	1.60	0.055	0.059	0.063
D1	1.40	1.50	1.60	0.055	0.059	0.063
P0	3.90	4.00	4.10	0.154	0.157	0.161
P1	7.90	8.00	8.10	0.311	0.315	0.319
P2	1.90	2.00	2.10	0.075	0.079	0.083
A0	6.85	6.90	7.00	0.270	0.271	0.276
B0	10.45	10.50	10.60	0.411	0.413	0.417
K0	2.68	2.78	2.88	0.105	0.109	0.113
T	0.24		0.27	0.009		0.011
t1	0.10			0.004		
10P0	39.80	40.00	40.20	1.567	1.575	1.583